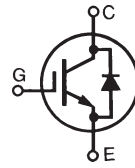
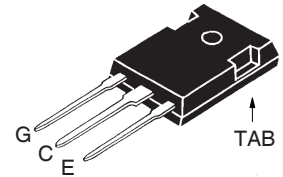


**GenX3™ C3-Class  
IGBT w/Diode**
**IXGH40N120C3D1**

$$\begin{aligned}
 V_{CES} &= 1200V \\
 I_{C110} &= 40A \\
 V_{CE(sat)} &\leq 4.4V \\
 t_{fi(typ)} &= 57ns
 \end{aligned}$$

**High Speed PT IGBT  
for 20 - 50 kHz Switching**


Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	1200	V
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GE} = 1M\Omega$	1200	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$ (Limited by Leads)	75	A
$I_{C110}$	$T_C = 110^\circ\text{C}$	40	A
$I_{F110}$	$T_C = 110^\circ\text{C}$	25	A
$I_{CM}$	$T_C = 25^\circ\text{C}$ , 1ms	180	A
$I_A$	$T_C = 25^\circ\text{C}$	30	A
$E_{AS}$	$T_C = 25^\circ\text{C}$	500	mJ
<b>SSOA</b>	$V_{GE} = 15V$ , $T_J = 125^\circ\text{C}$ , $R_G = 3\Omega$	$I_{CM} = 80$	A
<b>(RBSOA)</b>	Clamped inductive load	@ $V_{CE} \leq 1200$	V
$P_C$	$T_C = 25^\circ\text{C}$	380	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$M_d$	Mounting Torque	1.13 / 10	Nm/lb.in.
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
$T_{SOLD}$	1.6mm (0.062 in.) from Case for 10s	260	$^\circ\text{C}$
<b>Weight</b>		6	g

**TO-247**


G = Gate      C = Collector  
E = Emitter    TAB = Collector

**Features**

- Optimized for Low Conduction Losses
- Square RBSOA
- Avalanche Rated
- Anti-Parallel Ultra Fast Diode
- International Standard Package

**Advantages**

- High Power Density
- Low Gate Drive Requirement

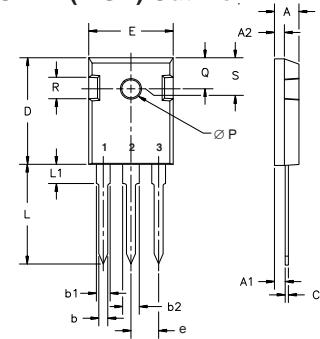
**Applications**

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- DC Choppers
- AC Motor Drives
- DC Servo and Robot Drives

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$V_{GE(th)}$	$I_C = 250\mu\text{A}$ , $V_{CE} = V_{GE}$	3.0		5.0 V
$I_{CES}$	$V_{CE} = V_{CES}$ , $V_{GE} = 0V$ $T_J = 125^\circ\text{C}$			100 $\mu\text{A}$ 3 mA
$I_{GES}$	$V_{CE} = 0V$ , $V_{GE} = \pm 20V$			$\pm 100$ nA
$V_{CE(sat)}$	$I_C = 30A$ , $V_{GE} = 15V$ , Note 1 $T_J = 125^\circ\text{C}$		2.7	4.4 V V

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$I_C = 30A, V_{CE} = 10V$ , Note 1	18	30	S
$C_{ies}$	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		2930	pF
$C_{oes}$			240	pF
$C_{res}$			93	pF
$Q_g$	$I_C = 40A, V_{GE} = 15V, V_{CE} = 0.5 \cdot V_{CES}$		142	nC
$Q_{ge}$			19	nC
$Q_{gc}$			62	nC
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ C</math></b> $I_C = 30A, V_{GE} = 15V$ $V_{CE} = 600V, R_G = 3\Omega$ Note 2		17	ns
$t_{ri}$			33	ns
$E_{on}$			1.80	mJ
$t_{d(off)}$			130	ns
$t_{fi}$			57	100 ns
$E_{off}$			0.55	1.00 mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ C</math></b> $I_C = 30A, V_{GE} = 15V$ $V_{CE} = 600V, R_G = 3\Omega$ Note 2		17	ns
$t_{ri}$			35	ns
$E_{on}$			3.50	mJ
$t_{d(off)}$			177	ns
$t_{fi}$			298	ns
$E_{off}$			1.60	mJ
$R_{thJC}$				0.33 °C/W
$R_{thCK}$		0.21		°C/W

TO-247 (IXGH) Outline



Terminals: 1 - Gate 2 - Drain  
3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

### Reverse Diode (FRED)

( $T_J = 25^\circ C$ , Unless Otherwise Specified)

Symbol	Test Conditions	Characteristic Value		
		Min.	Typ.	Max.
$V_F$	$I_F = 30A, V_{GE} = 0V$ , Note 1		1.6	2.8 V
		$T_J = 150^\circ C$		V
$I_{RM}$	$I_F = 30A, V_{GE} = 0V, -di_F/dt = 100A/\mu s, T_J = 100^\circ C$			4 A
$t_{rr}$		$V_R = 300V, T_J = 100^\circ C$		100
$R_{thJC}$				0.9 °C/W

Note 1: Pulse Test,  $t \leq 300\mu s$ , Duty Cycle,  $d \leq 2\%$ .

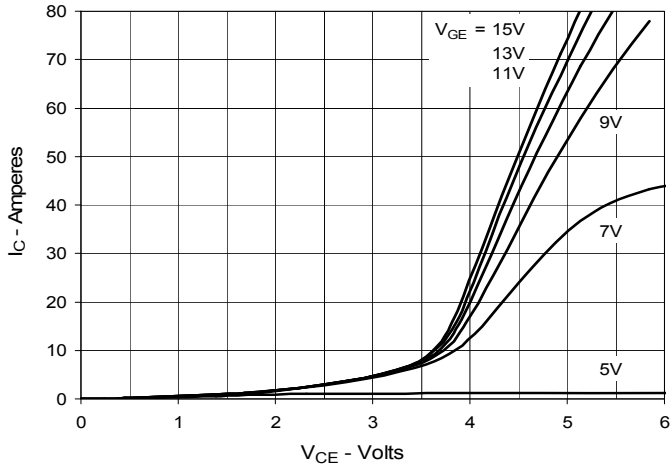
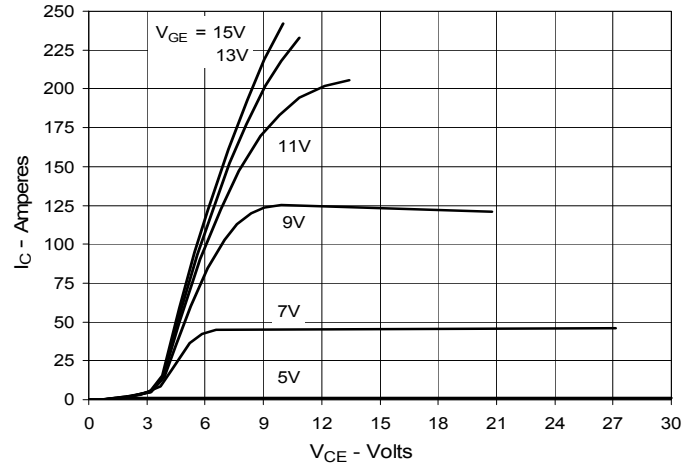
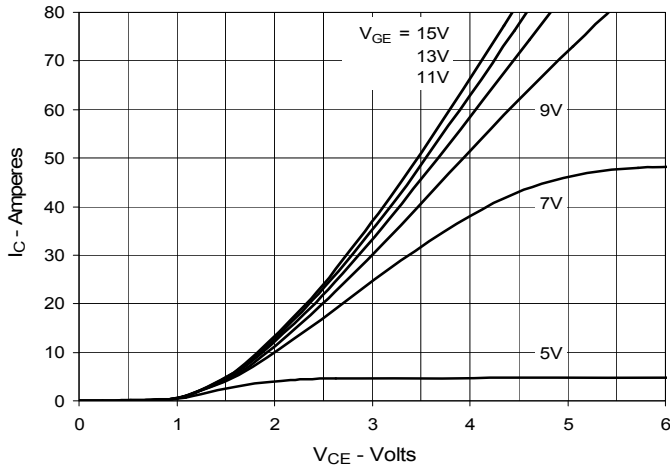
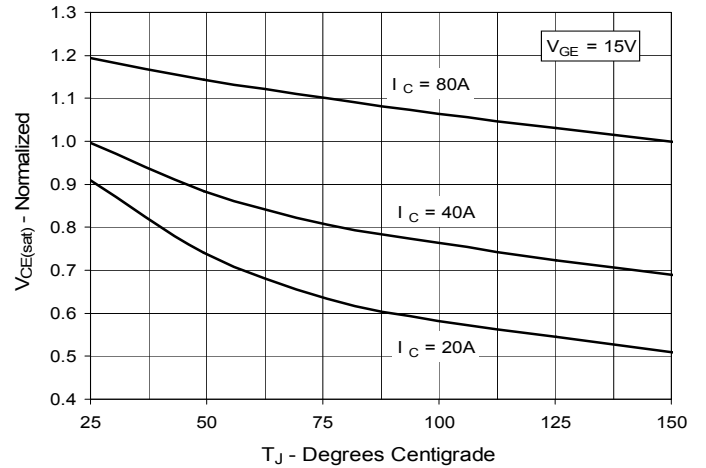
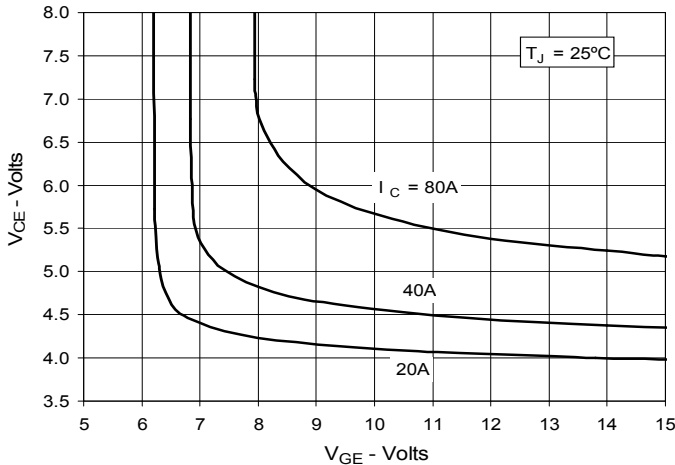
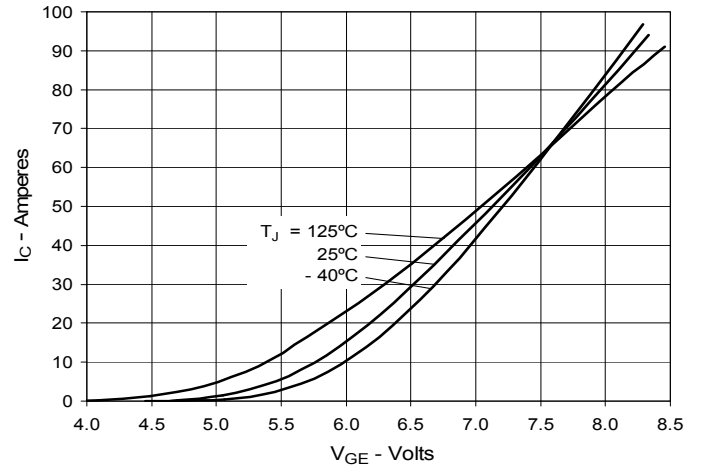
2. Switching Times may Increase for  $V_{CE}$  (Clamp)  $> 0.5 V_{CES}$ , Higher  $T_J$  or Increased  $R_G$ .

### PRELIMINARY TECHNICAL INFORMATION

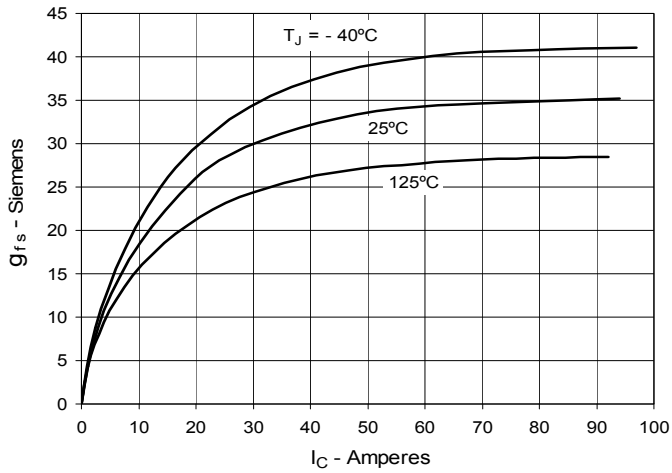
The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

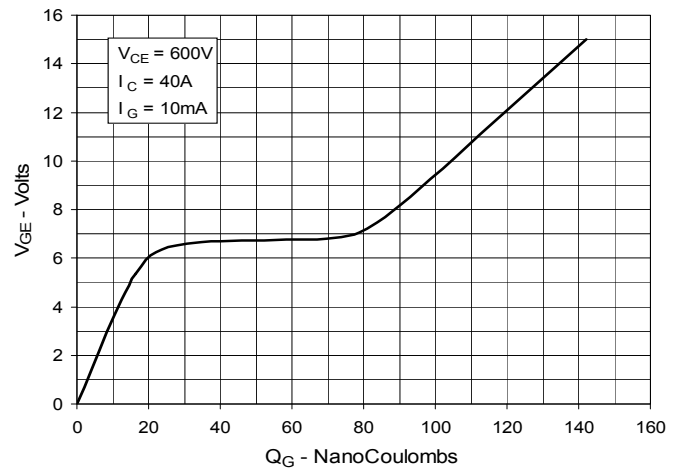
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics  
@ 25°C**

**Fig. 2. Extended Output Characteristics  
@ 25°C**

**Fig. 3. Output Characteristics  
@ 125°C**

**Fig. 4. Dependence of  $V_{CE(sat)}$  on  
Junction Temperature**

**Fig. 5. Collector-to-Emitter Voltage  
vs. Gate-to-Emitter Voltage**

**Fig. 6. Input Admittance**


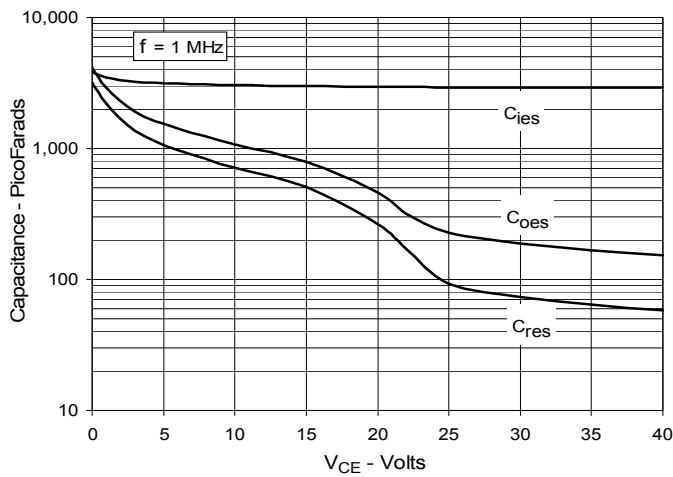
**Fig. 7. Transconductance**



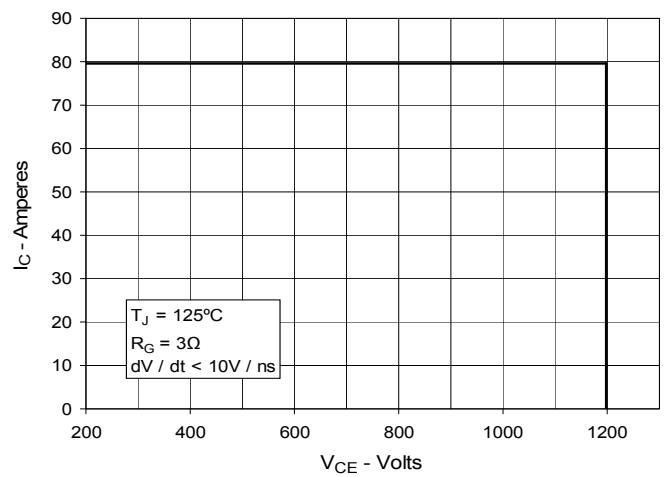
**Fig. 8. Gate Charge**



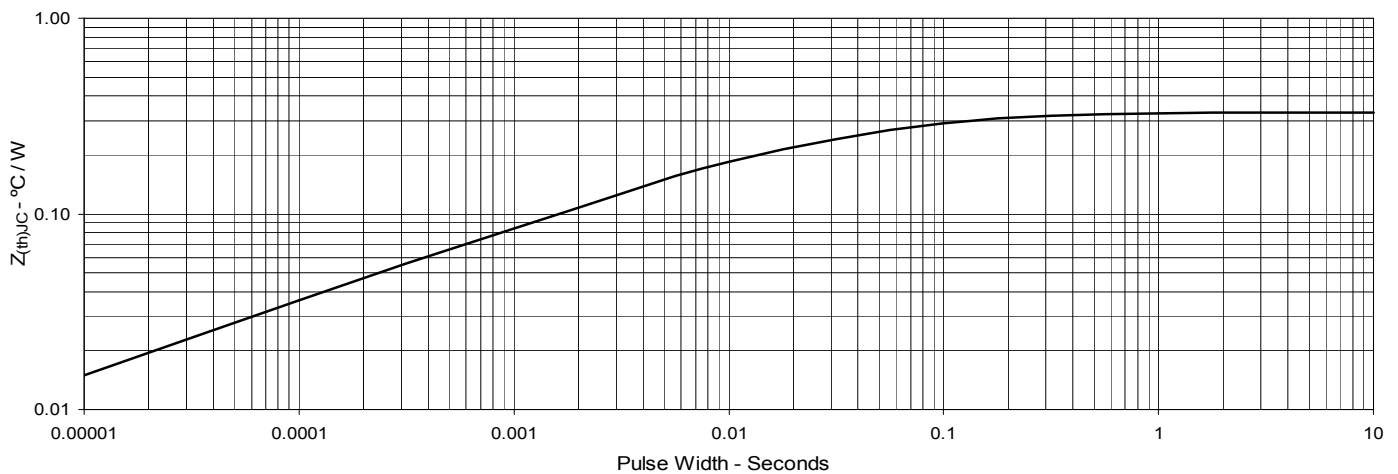
**Fig. 9. Capacitance**

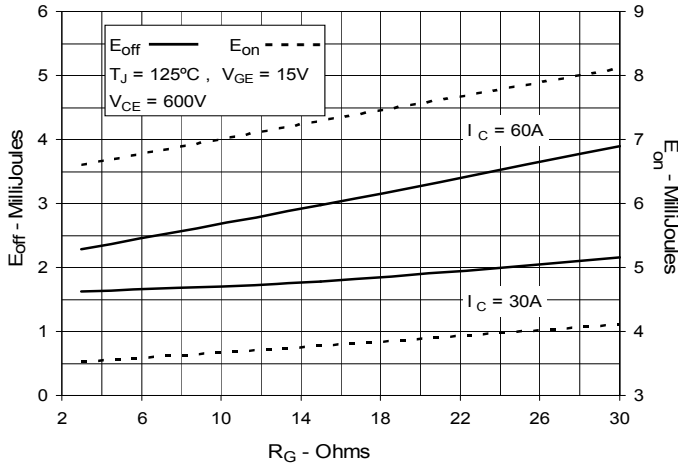
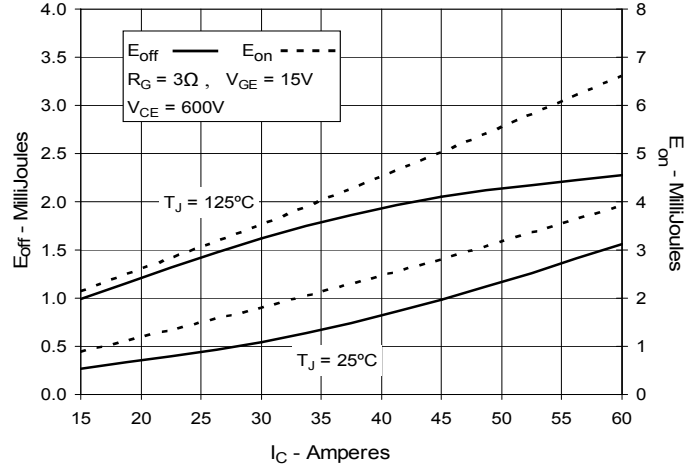
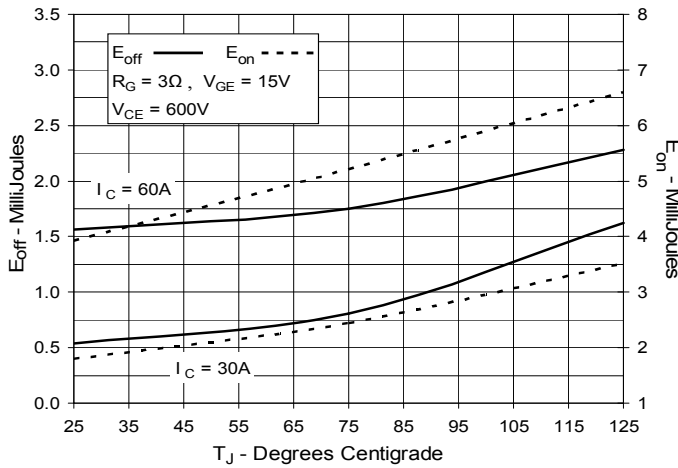
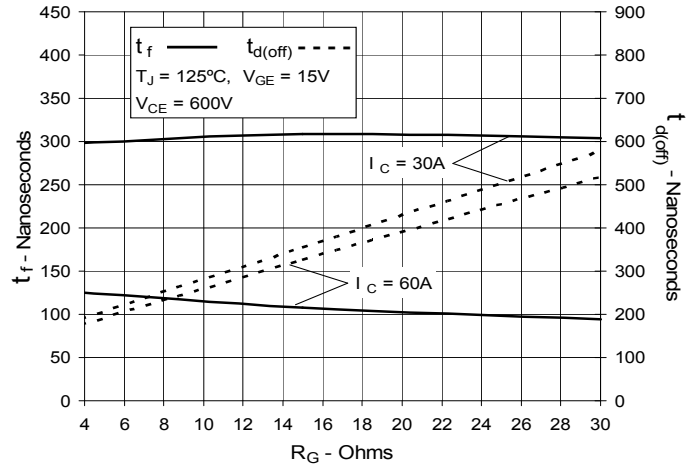
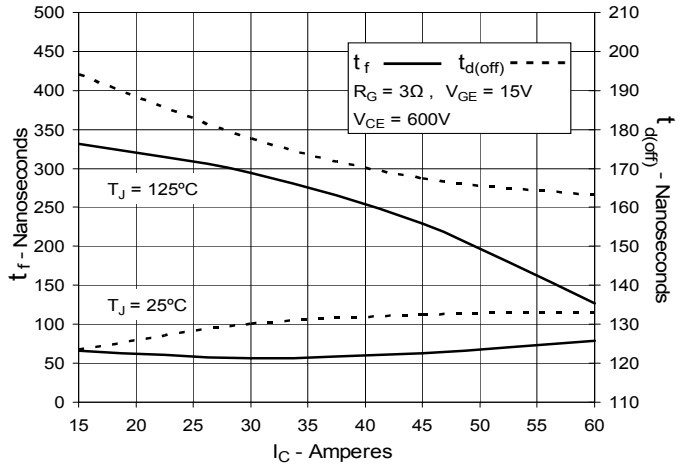
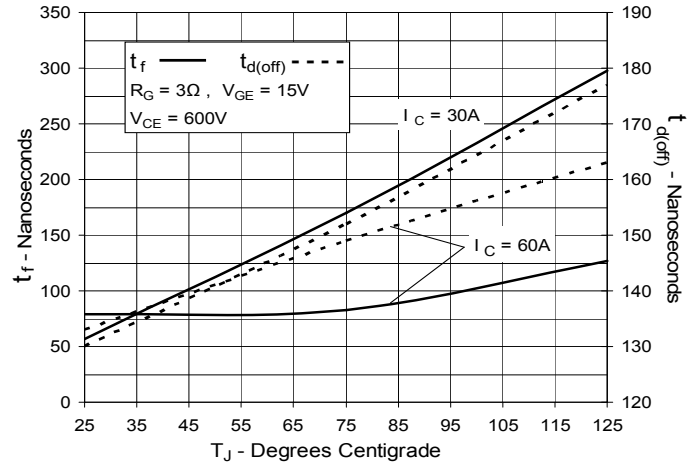


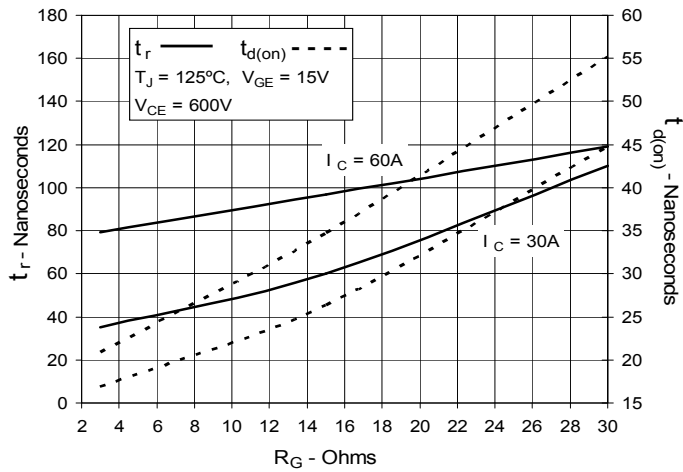
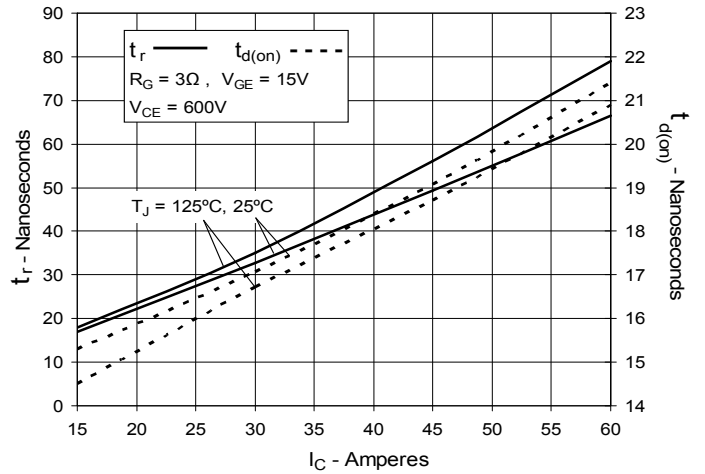
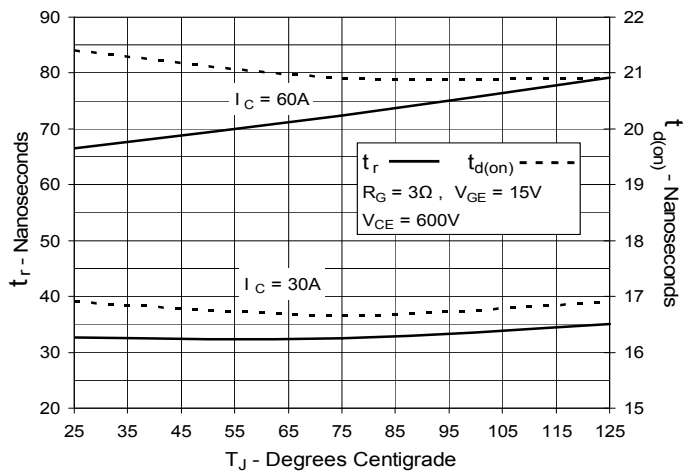
**Fig. 10. Reverse-Bias Safe Operating Area**



**Fig. 11. Maximum Transient Thermal Impedance**



**Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance**

**Fig. 13. Inductive Switching Energy Loss vs. Collector Current**

**Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature**

**Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance**

**Fig. 16. Inductive Turn-off Switching Times vs. Collector Current**

**Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature**


**Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance**

**Fig. 19. Inductive Turn-on Switching Times vs. Collector Current**

**Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature**


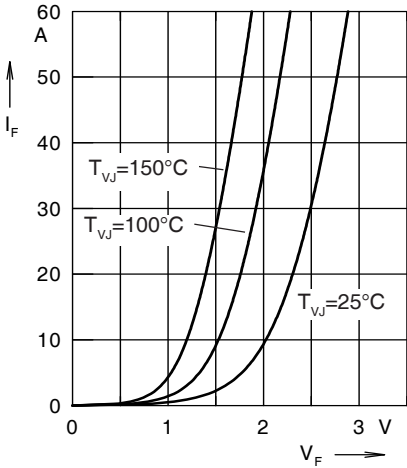


Fig. 21. Forward Current  $I_F$  Versus  $V_F$

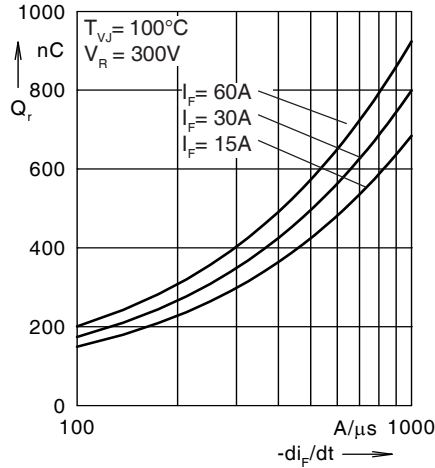


Fig. 22. Reverse Recovery Charge  $Q_r$  Versus  $-di_F/dt$

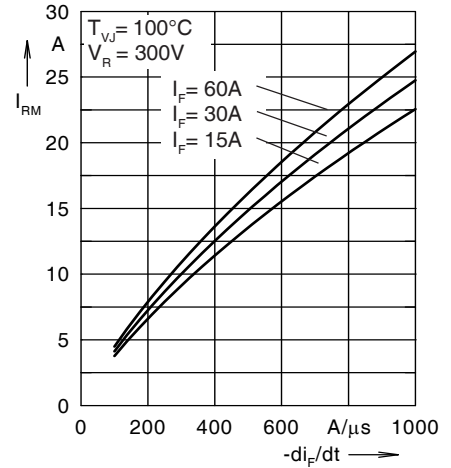


Fig. 23. Peak Reverse Current  $I_{RM}$  Versus  $-di_F/dt$

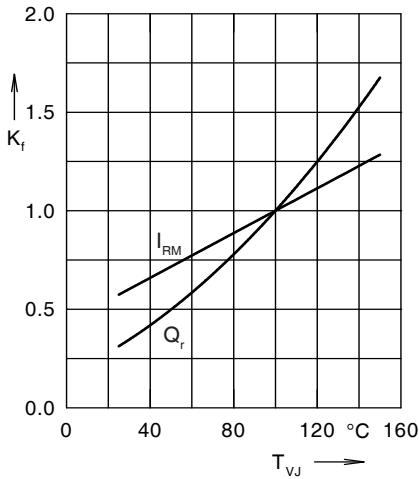


Fig. 24. Dynamic Parameters  $Q_r$ ,  $I_{RM}$  Versus  $T_{VJ}$

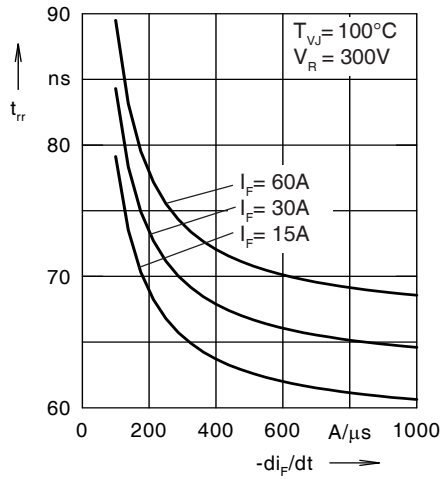


Fig. 25. Recovery Time  $t_{tr}$  Versus  $-di_F/dt$

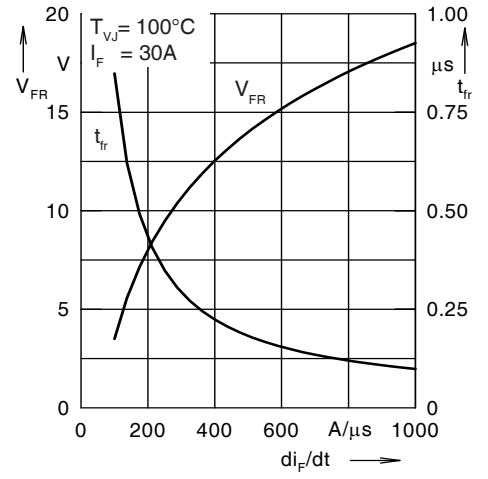


Fig. 26. Peak Forward Voltage  $V_{FR}$  and  $t_{tr}$  Versus  $di_F/dt$

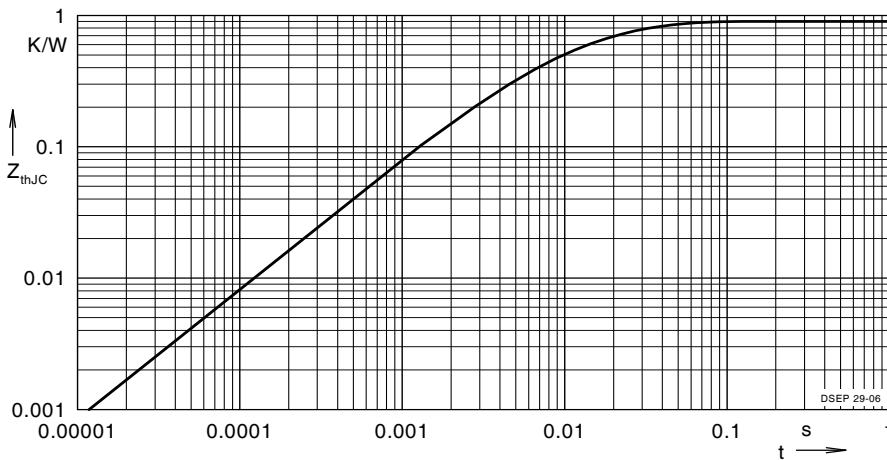


Fig. 27. Transient Thermal Resistance Junction to Case



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